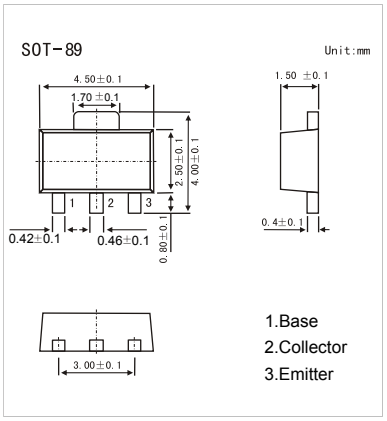
PNP Transistors

2SA1483



■ Features

- High transition frequency
- Low collector output capacitance
- Complementary to 2SC3803

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-60	V
Collector - Emitter Voltage	V_{CEO}	-45	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-200	mA
Base Current	I_B	-50	
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA, I_E=0	-60			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -0.5 mA, I_B= 0	-45			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μA, I_C=0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -45 V , I_E=0			-0.1	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100 mA, I_B=-10 mA			-0.3	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-100 mA, I_B=-10 mA			-1	
Input impedance (real part)	$R_{e(hie)}$	V_{CB}= -10V, I_E=10mA,f=200MHz			120	Ω
DC current gain	h_{FE}	V_{CE}= -1V, I_C= -10mA	40		240	
		V_{CE}= -3V, I_C= -200mA	20			
Turn-on time	t_{on}	See Test Circuit.		40		ns
Storage time	t_{stg}			250		
Fall time	t_f			30		
Collector output capacitance	C_{ob}	V_{CB}= -10V, I_E= 0,f=1MHz		3.5	5	pF
Transition frequency	f_T	V_{CE}= -10V, I_C= -10mA	100	200		MHz

■ Classification of $h_{fe(1)}$

Type	2SA1483-R	2SA1483-O	2SA1483-Y
Range	40-80	70-140	120-240
Marking	WR*	WO*	WY*

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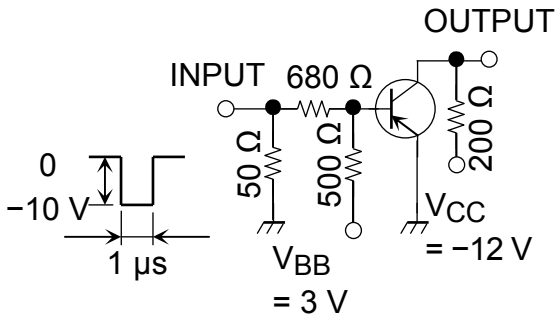
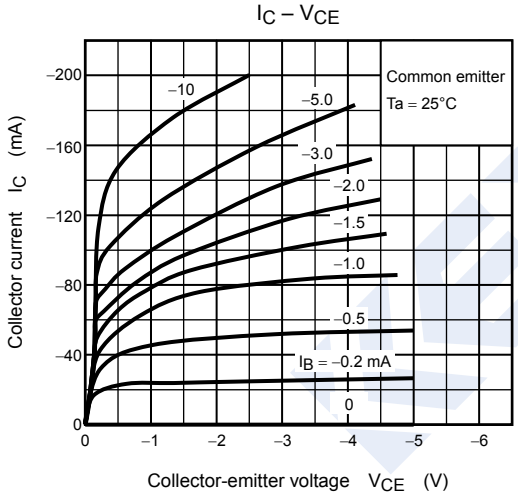
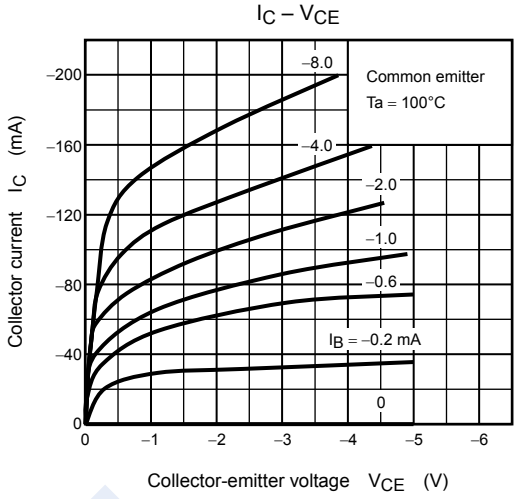
Switching Time Test Circuit

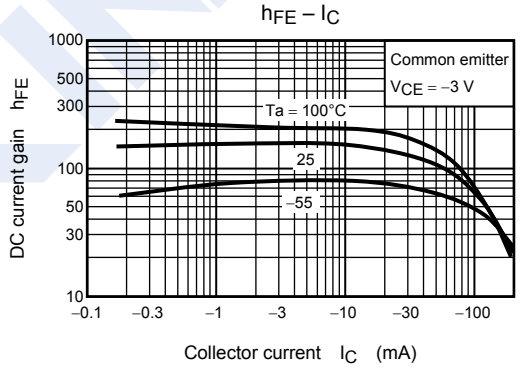


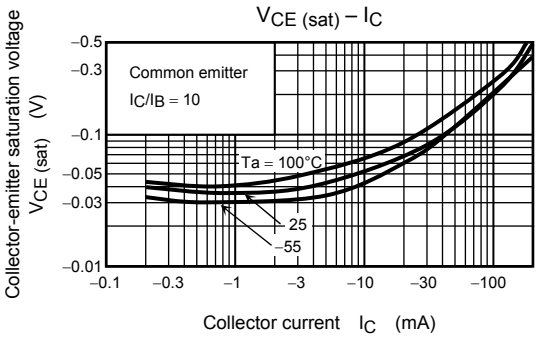
DUTY CYCLE ≤ 2%

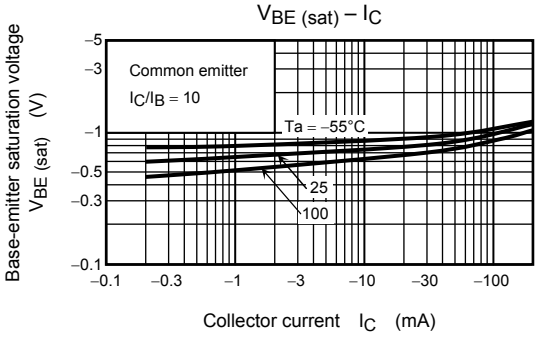
■ Typical Characterisitics











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■ Typical Characterisitics